

NTLJF4156N

Power MOSFET and Schottky Diode

30 V, 4.6 A, μ Cool™ N-Channel, with
2.0 A Schottky Barrier Diode, 2x2 mm
WDFN Package

Features

- WDFN Package Provides Exposed Drain Pad for Excellent Thermal Conduction
- Co-Packaged MOSFET and Schottky For Easy Circuit Layout
- $R_{DS(on)}$ Rated at Low $V_{GS(on)}$ Levels, $V_{GS} = 1.5$ V
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments
- Low V_F Schottky
- This is a Pb-Free Device

Applications

- DC-DC Converters
- Li-Ion Battery Applications in Cell Phones, PDA's, Media Players
- Color Display and Camera Flash Regulators

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	30	V
Gate-to-Source Voltage		V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	I_D	$T_J = 25^\circ\text{C}$	A
			$T_J = 85^\circ\text{C}$	
	$t \leq 5$ s		$T_J = 25^\circ\text{C}$	
Power Dissipation (Note 1)	Steady State	P_D	$T_J = 25^\circ\text{C}$	W
	$t \leq 5$ s			
Continuous Drain Current (Note 2)	Steady State	I_D	$T_J = 25^\circ\text{C}$	A
			$T_J = 85^\circ\text{C}$	
Power Dissipation (Note 2)	Steady State	P_D	$T_J = 25^\circ\text{C}$	0.71
Pulsed Drain Current	$t_p = 10$ μ s	I_{DM}	20	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		I_S	2.4	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm², 2 oz. Cu.



ON Semiconductor®

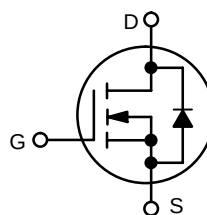
<http://onsemi.com>

MOSFET

$V_{(BR)DS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
30 V	70 m Ω @ 4.5 V	4.6 A
	90 m Ω @ 2.5 V	
	125 m Ω @ 1.8 V	
	250 m Ω @ 1.5 V	

SCHOTTKY DIODE

V_R MAX	V_F TYP	I_F MAX
30 V	0.47 V	2.0 A



N-CHANNEL MOSFET



SCHOTTKY DIODE



WDFN6
CASE 506AN

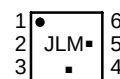
JL = Specific Device Code

M = Date Code

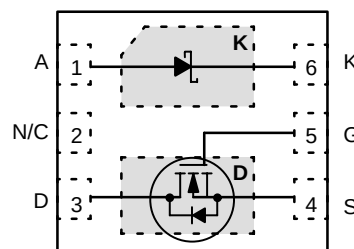
■ = Pb-Free Package

(Note: Microdot may be in either location)

MARKING DIAGRAM



PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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SCHOTTKY DIODE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
DC Blocking Voltage	V_R	30	V
Average Rectified Forward Current	I_F	2.0	A

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	83	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	54	
Junction-to-Ambient – Steady State Min Pad (Note 4)	$R_{\theta JA}$	180	

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
 4. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm², 2 oz. Cu.

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250$ μA , Ref to 25°C		18.1		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24$ V, $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 85^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 8.0$ V			100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250$ μA	0.4	0.7	1.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.8		mV/ $^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5$, $I_D = 2.0$ A		47	70	m Ω
		$V_{GS} = 2.5$, $I_D = 2.0$ A		56	90	
		$V_{GS} = 1.8$, $I_D = 1.8$ A		88	125	
		$V_{GS} = 1.5$, $I_D = 1.5$ A		133	250	
Forward Transconductance	g_{FS}	$V_{DS} = 10$ V, $I_D = 2.0$ A		4.5		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1.0$ MHz, $V_{DS} = 15$ V		427		pF
Output Capacitance	C_{OSS}			51		
Reverse Transfer Capacitance	C_{RSS}			32		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 2.0$ A		5.4	6.5	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.5		
Gate-to-Source Charge	Q_{GS}			0.8		
Gate-to-Drain Charge	Q_{GD}			1.24		
Gate Resistance	R_G			3.7		Ω

5. Pulse Test: Pulse Width ≤ 300 μs , Duty Cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

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MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 6)						
Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 15 V, I _D = 2.0 A, R _G = 2.0 Ω		4.8		ns
Rise Time	t _r			9.2		
Turn-Off Delay Time	t _{d(OFF)}			14.2		
Fall Time	t _f			1.7		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Recovery Voltage	V _{SD}	V _{GS} = 0 V, I _S = 2.0 A	T _J = 25°C		0.78	1.2	V
			T _J = 125°C		0.62		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dI _t = 100 A/μs, I _S = 2.0 A			10.5		ns
Charge Time	t _a				7.6		
Discharge Time	t _b				2.9		
Reverse Recovery Time	Q _{RR}				5.0		nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

6. Switching characteristics are independent of operating junction temperatures.

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V _F	I _F = 0.1 A		0.34	0.39	V
		I _F = 1.0 A		0.47	0.53	
Maximum Instantaneous Reverse Current	I _R	V _R = 30 V		17	20	μA
		V _R = 20 V		3.0	8.0	
		V _R = 10 A		2.0	4.5	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS (T_J = 85°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V _F	I _F = 0.1 A		0.22	0.35	V
		I _F = 1.0 A		0.40	0.50	
Maximum Instantaneous Reverse Current	I _R	V _R = 30 V		0.22	2.5	mA
		V _R = 20 V		0.11	1.6	
		V _R = 10 V		0.06	1.2	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS (T_J = 125°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V _F	I _F = 0.1 A		0.2	0.29	V
		I _F = 1.0 A		0.4	0.47	
Maximum Instantaneous Reverse Current	I _R	V _R = 30 V		2.0	20	mA
		V _R = 20 V		1.1	10.9	
		V _R = 10 V		0.63	8.4	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Capacitance	C	V _R = 5.0 V, f = 1.0 MHz		38		pF

7. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

8. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm², 2 oz cu.

9. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

10. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

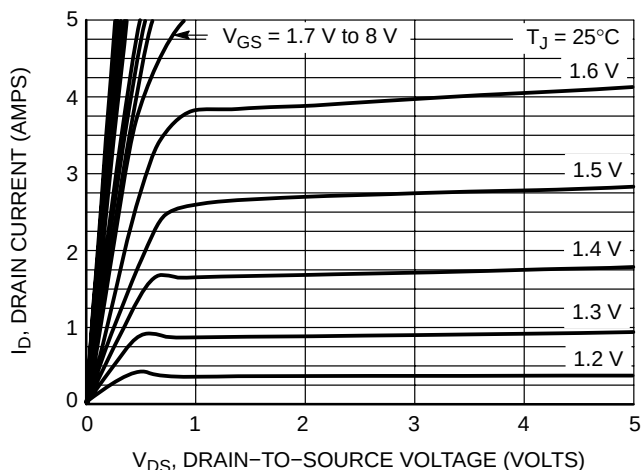


Figure 1. On-Region Characteristics

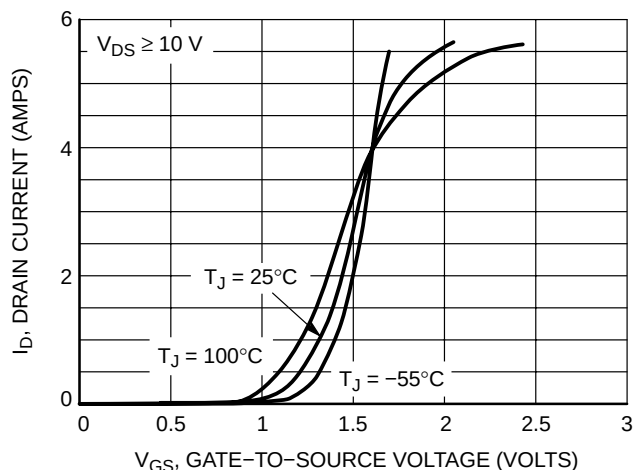


Figure 2. Transfer Characteristics

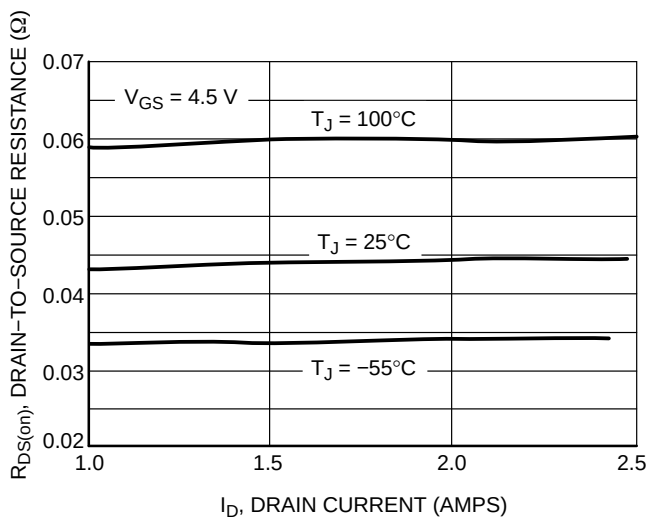


Figure 3. On-Resistance versus Drain Current

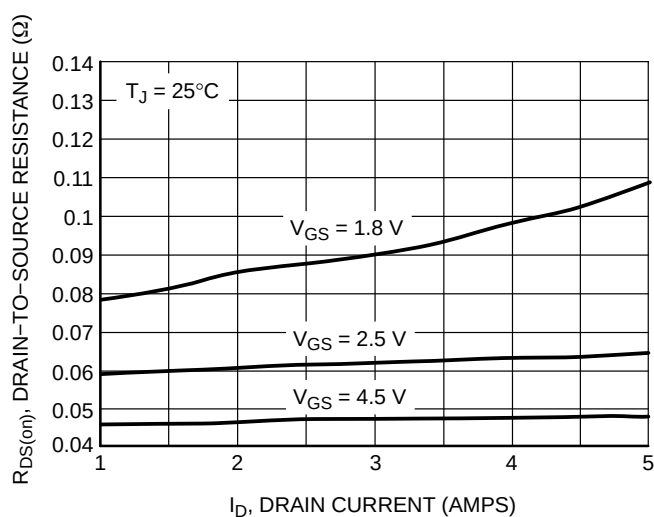


Figure 4. On-Resistance versus Drain Current and Gate Voltage

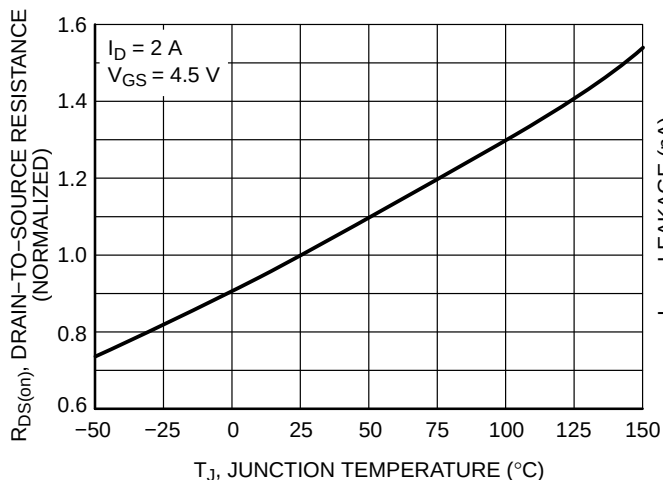


Figure 5. On-Resistance Variation with Temperature

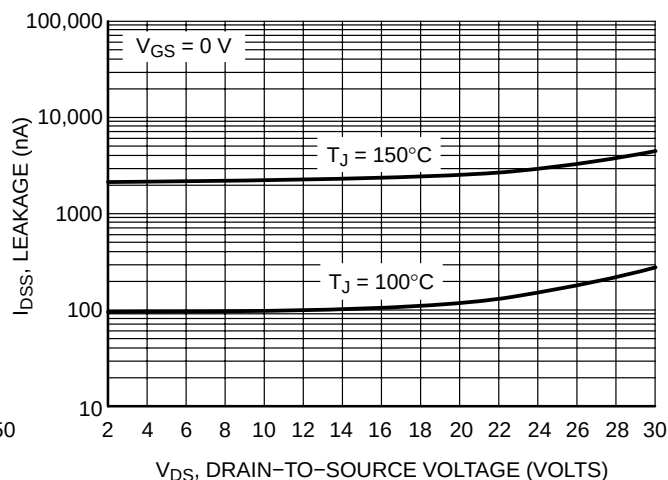


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

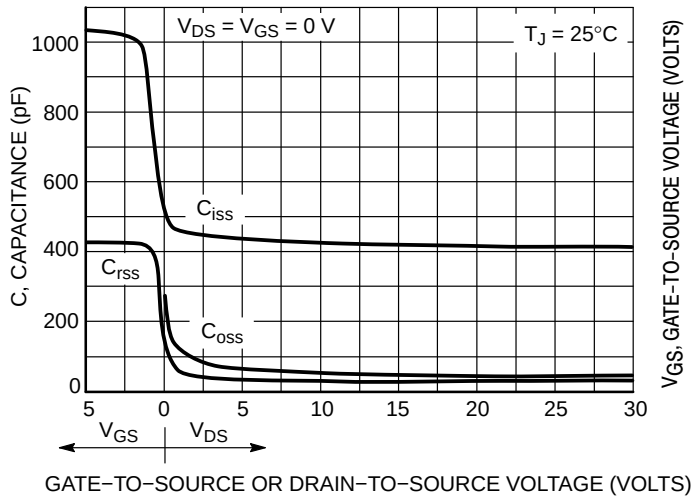


Figure 7. Capacitance Variation

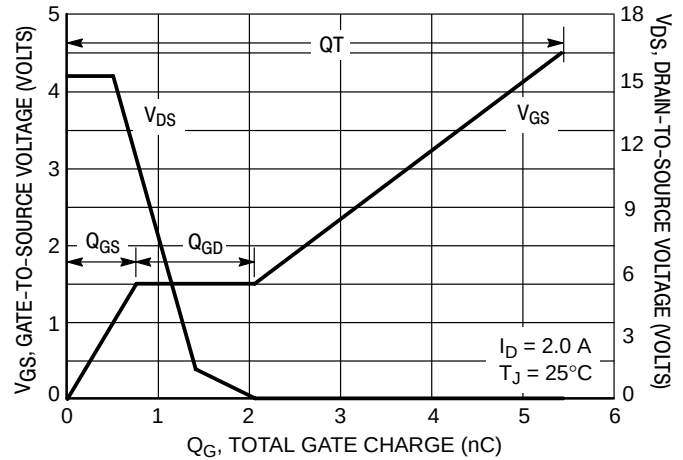


Figure 8. Gate-To-Source and Drain-To-Source Voltage versus Total Charge

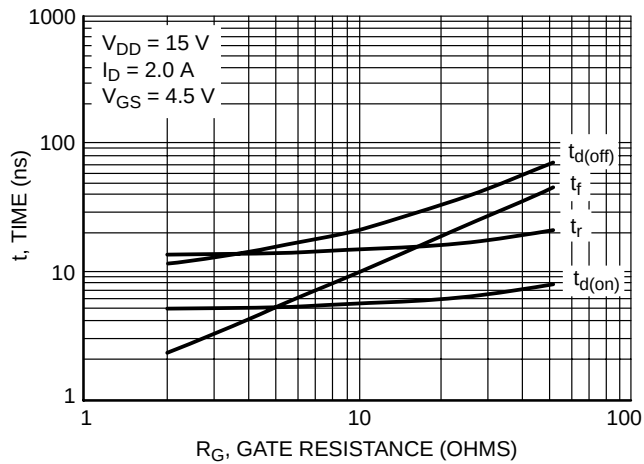


Figure 9. Resistive Switching Time Variation versus Gate Resistance

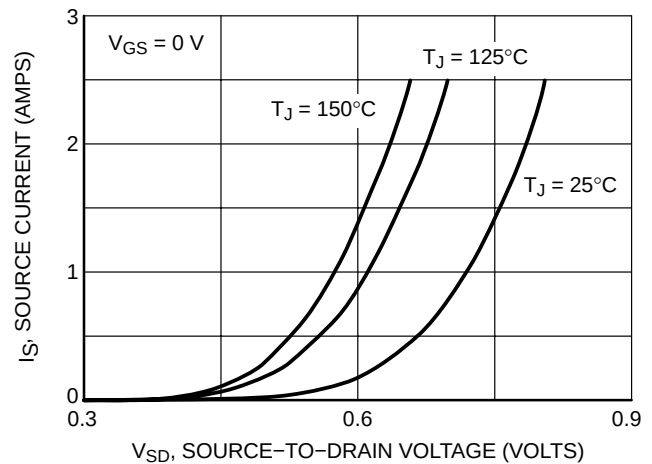


Figure 10. Diode Forward Voltage versus Current

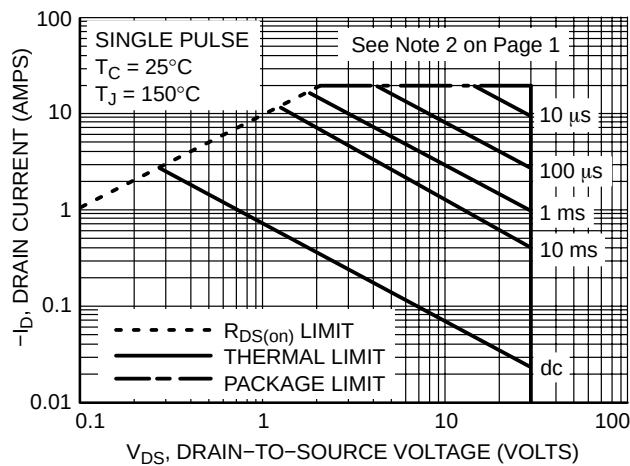


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

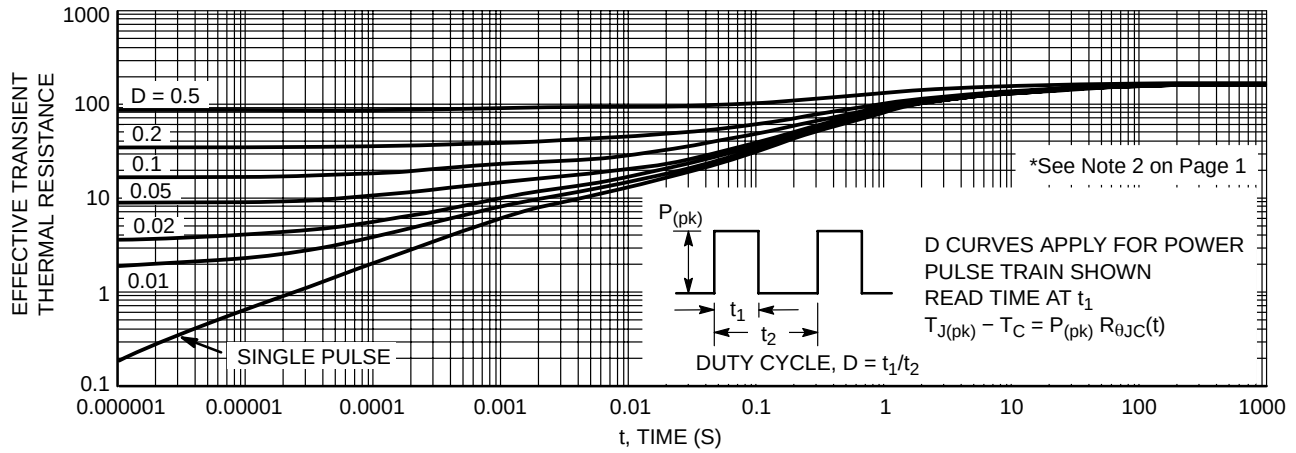


Figure 12. Thermal Response

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TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

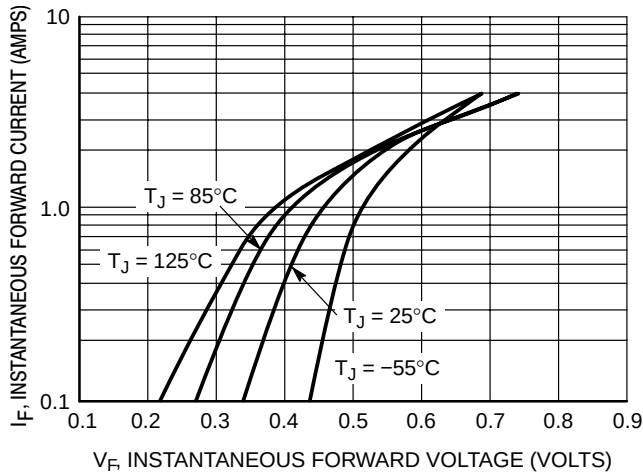


Figure 13. Typical Forward Voltage

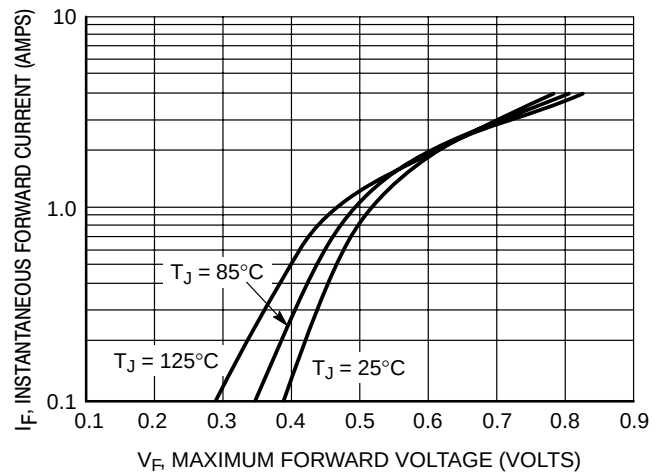


Figure 14. Maximum Forward Voltage

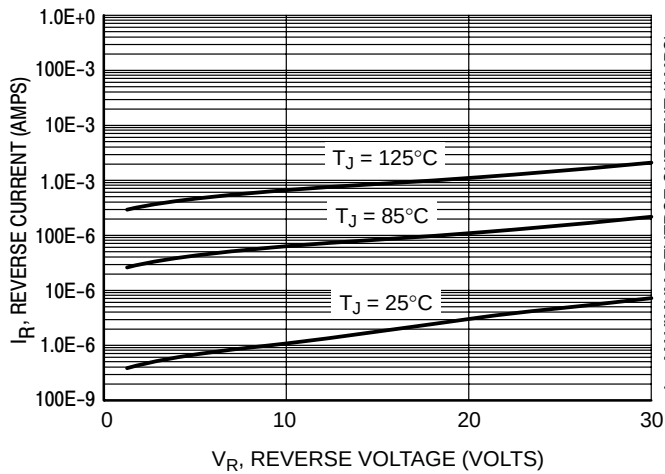


Figure 15. Typical Reverse Current

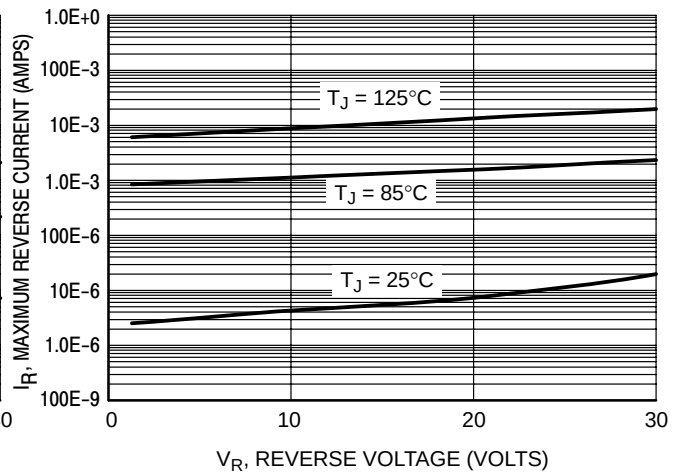


Figure 16. Maximum Reverse Current

ORDERING INFORMATION

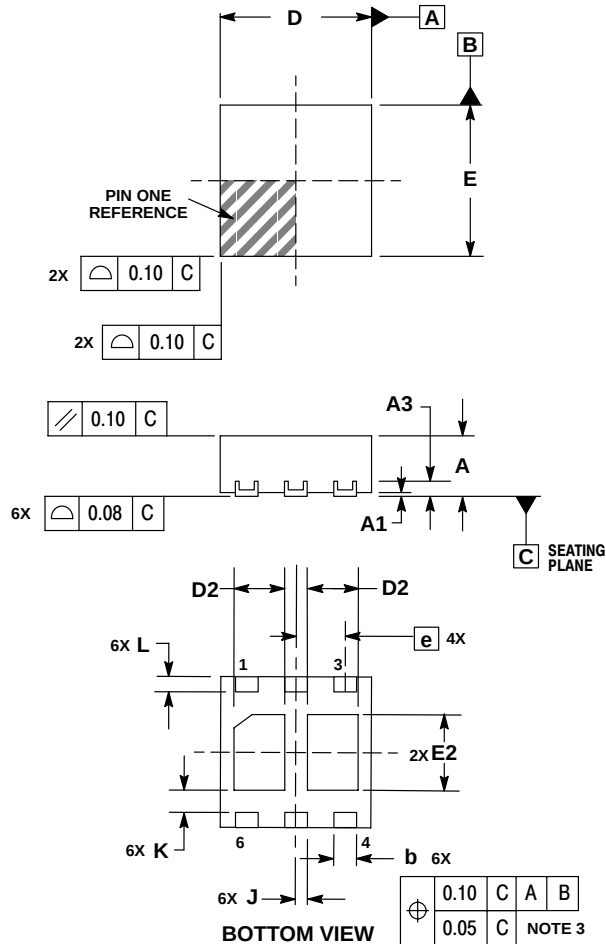
Device	Package	Shipping [†]
NTLJF4156NT1G	WDFN6 (Pb-Free)	3000 / Tape & Reel
NTLJF4156NTAG	WDFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTLJF4156N

PACKAGE DIMENSIONS

WDFN6, 2x2
CASE 506AN-01
ISSUE B

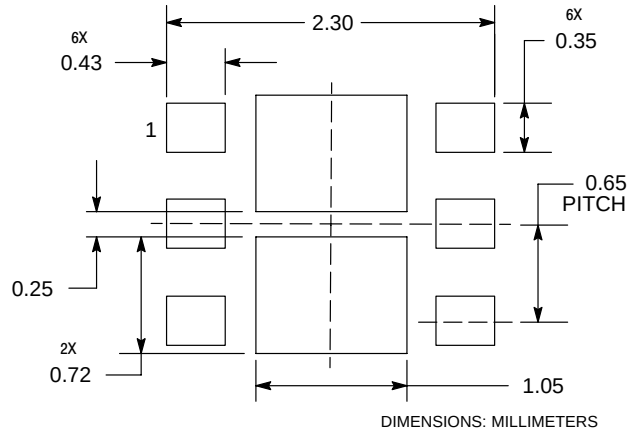


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.70	0.80
A1	0.00	0.05
A3	0.20 REF	
b	0.25	0.35
D	2.00 BSC	
D2	0.57	0.77
E	2.00 BSC	
E2	0.90	1.10
e	0.65 BSC	
K	0.25 REF	
L	0.20	0.30
J	0.15 REF	

SOLDERMASK DEFINED MOUNTING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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NTLJF4156N/D



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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